优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码

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Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = 25°C
100V	85mΩ @ V_{GS} = 10V	7.7A
	100mΩ @ V_{GS} = 6V	7.1A

Description and Applications

This MOSFET features low on-resistance, fast switching and a high avalanche withstand capability, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions
- Disconnect switches
- Motor control
- Uninterrupted power supply

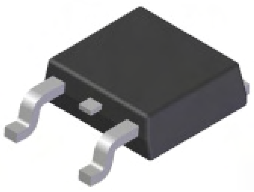
Features and Benefits

- Low input capacitance
- Low on-resistance
- Fast switching speed

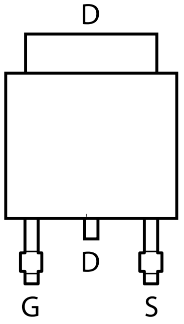
Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic “Green” Molding Compound, UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

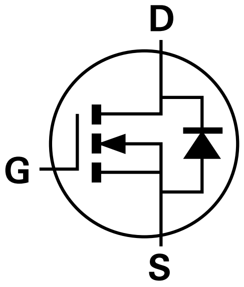
TO252-3L



Top View



Pin Out – Top View



Equivalent Circuit

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	100	V
Gate-Source voltage			V_{GS}	±20	V
Continuous Drain current	V_{GS} = 10V	(Note 3) T_A = 70°C (Note 3) (Note 2)	I_D	7.7 6.2 5.0	A
Pulsed Drain current	V_{GS} = 10V	(Note 4)	I_{DM}	27	A
Continuous Source current (Body diode)		(Note 3)	I_S	11	A
Pulsed Source current (Body diode)		(Note 4)	I_{SM}	27	A

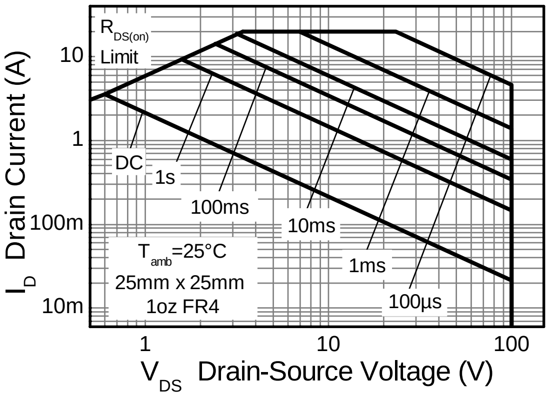
Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 2)	P_D	4.31 34.4	W mW/°C
	(Note 3)		10.1 80.8	
	(Note 6)		2.15 17.2	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	29	°C/W
	(Note 3)		12.3	
	(Note 6)		58	
Thermal Resistance, Junction to Lead	(Note 5)	$R_{\theta JL}$	1.14	°C/W
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	°C

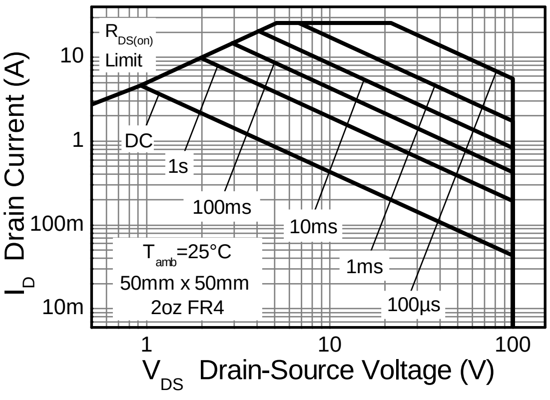
Notes:

2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
3. Same as note 2, except the device is measured at t ≤ 10 sec.
4. Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
5. Thermal resistance from junction to solder-point (at the end of the drain lead).
6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with the high coverage single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

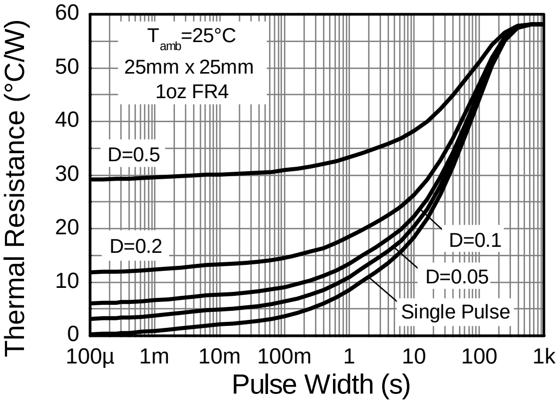
Thermal Characteristics



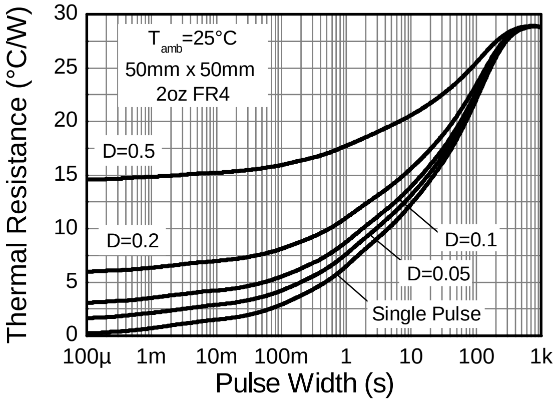
Safe Operating Area



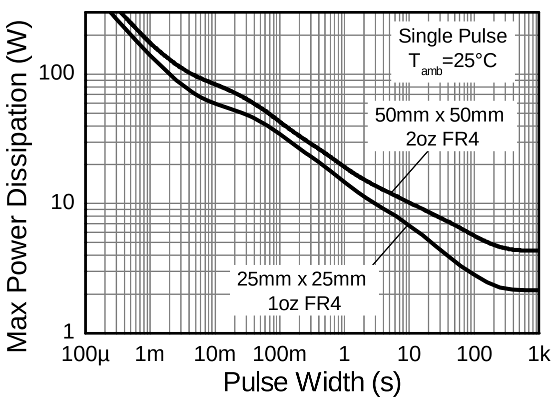
Safe Operating Area



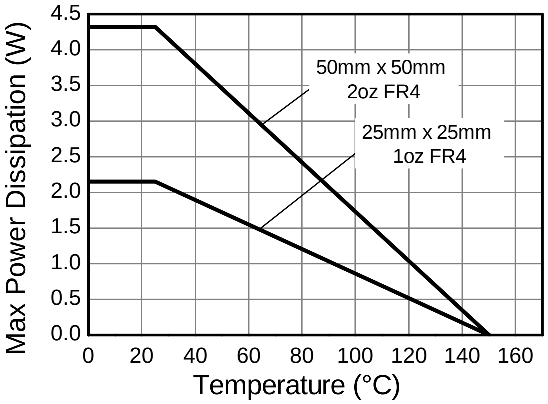
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve

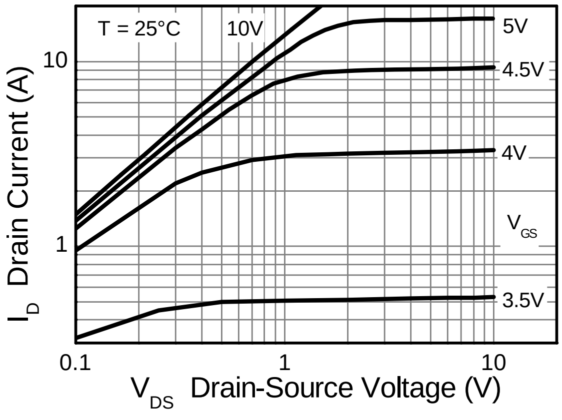
Electrical Characteristics

@T_A = 25°C unless otherwise specified

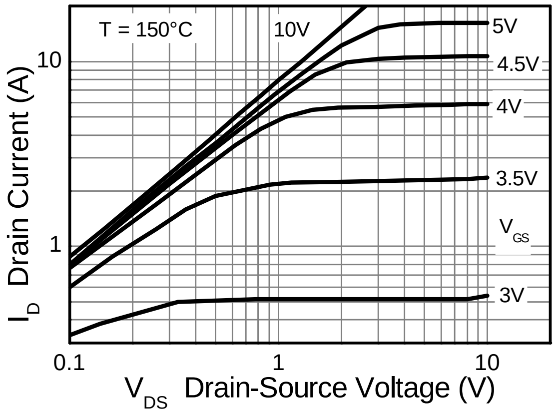
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	I_D = 250µA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 100V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	2	—	4	V	I_D = 250µA, V_{DS} = V_{GS}
Static Drain-Source On-Resistance (Note 7)	$R_{DS\ (ON)}$	—	—	0.085	Ω	V_{GS} = 10V, I_D = 4.6A
				0.100		V_{GS} = 6V, I_D = 4.2A
Forward Transconductance (Notes 7 & 8)	g_{fs}	—	10.7	—	S	V_{DS} = 15V, I_D = 4.6A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.850	0.950	V	I_S = 4.7A, V_{GS} = 0V
Reverse recovery time (Note 8)	t_{rr}	—	40	—	ns	I_S = 3.0A, di/dt = 100A/µs
Reverse recovery charge (Note 8)	Q_{rr}	—	62	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1313	—	pF	V_{DS} = 50V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	83	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	56	—	pF	
Total Gate Charge (Note 9)	Q_g	—	17.2	—	nC	V_{GS} = 6V V_{DS} = 50V, I_D = 4.6A
Total Gate Charge (Note 9)	Q_g	—	26.0	—	nC	V_{GS} = 10V
Gate-Source Charge (Note 9)	Q_{gs}	—	5.6	—	nC	
Gate-Drain Charge (Note 9)	Q_{gd}	—	7.6	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	—	6.8	—	ns	V_{DD} = 50V, V_{GS} = 10V I_D = 1.0A, $R_G \cong 25\Omega$
Turn-On Rise Time (Note 9)	t_r	—	5.3	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	—	27.5	—	ns	
Turn-Off Fall Time (Note 9)	t_f	—	12.3	—	ns	

Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
8. For design aid only, not subject to production testing.
9. Switching characteristics are independent of operating junction temperatures.

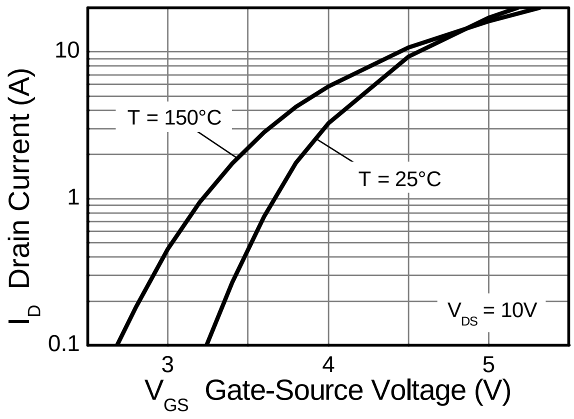
Typical Characteristics



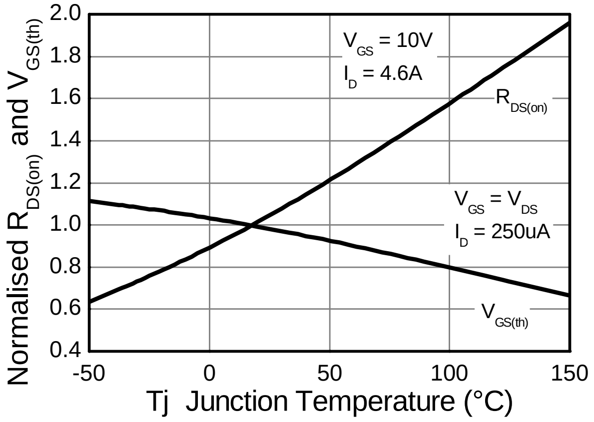
Output Characteristics



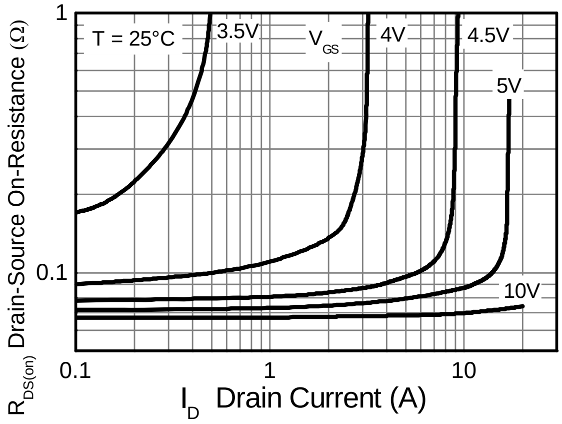
Output Characteristics



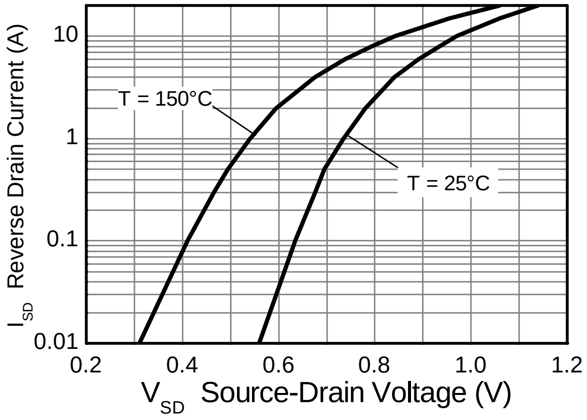
Typical Transfer Characteristics



Normalised Curves v Temperature

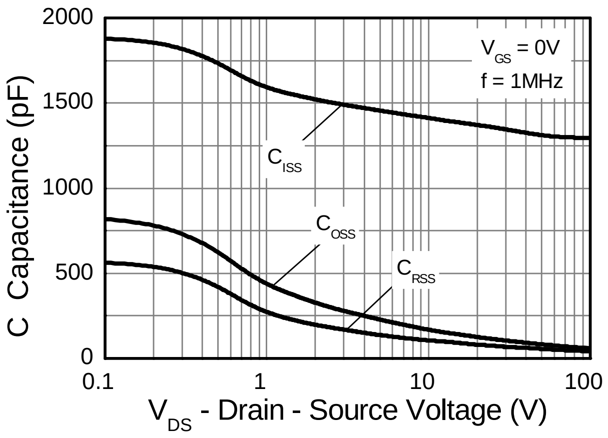


On-Resistance v Drain Current

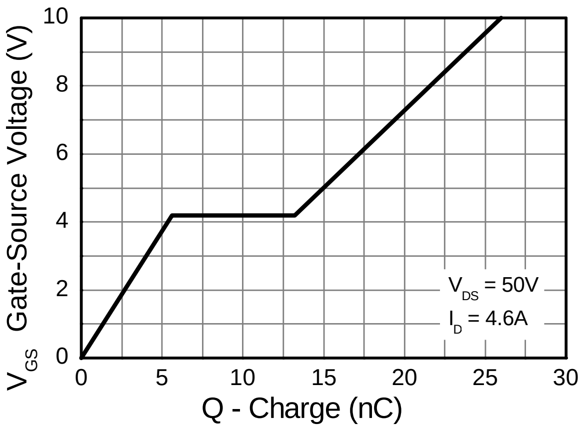


Source-Drain Diode Forward Voltage

Typical Characteristics - continued

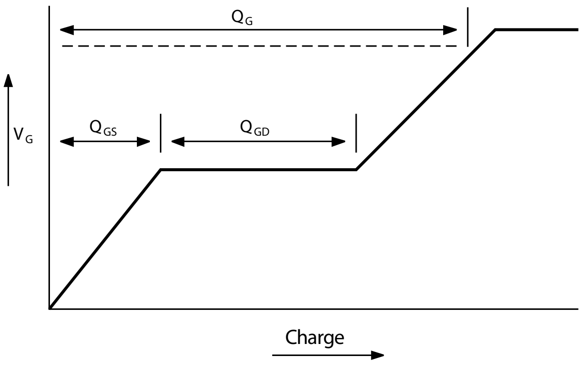


Capacitance v Drain-Source Voltage

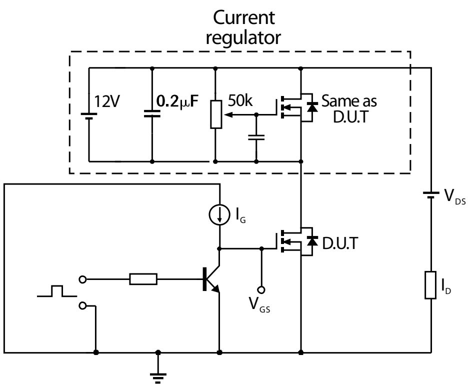


Gate-Source Voltage v Gate Charge

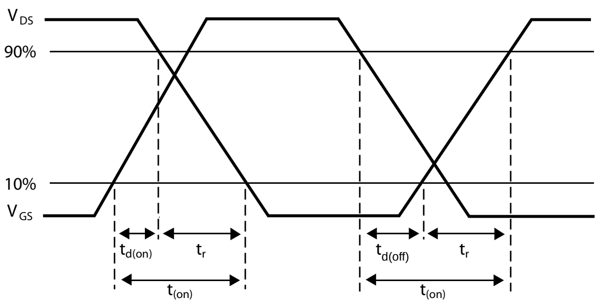
Test Circuits



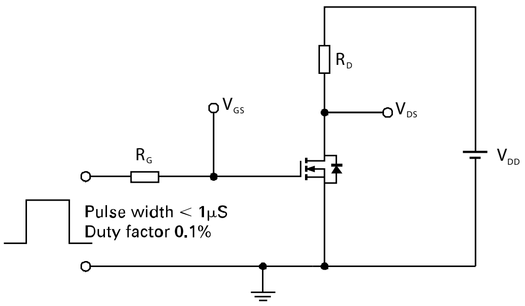
Basic gate charge waveform



Gate charge test circuit

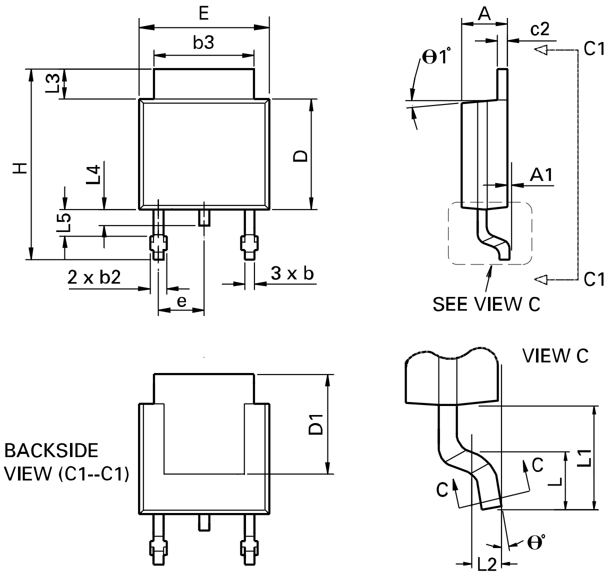


Switching time waveforms



Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	**e**	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	**H**	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	**L**	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	**L1**	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	**L2**	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	**L3**	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	**L4**	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	**L5**	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	**θ1°**	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	**θ°**	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Suggested Pad Layout